NSN 5961-01-426-3066

Diode Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-426-3066 **Inclosure Material:** Ceramic and metal **Overall Length:** Between 0.130 inches and 0.146 inches Overall Diameter: Between 0.063 inches and 0.067 inches **End Application:** Artu/dmu **Mounting Method:** Press fit **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 10.0 regulator voltage **Voltage Tolerance In Percent:** -5.0/+5.0 **Current Rating Per Characteristic:** 40.00 milliamperes repetitive peak forward current **Power Rating Per Characteristic:** 500.0 milliwatts small-signal input power, common-collector preset **Maximum Operating Tempurature Per Measurement Point:** 175.0 degrees celsius ambient air **Test Data Document:** 81349-mil-prf-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). **Terminal Type And Quantity:** 2 case **Specification Data:** 81349-mil-s-19500/127 government specification Shelf Life: N/a **Unit Of Measure: Demilitarization:** No Fiig:

Mil-std (military Standard): Mil-prf-19500 spec.

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